

APPLICATIONS

¶ Solar Applications

				Unit
				nA
				μ C
				nF
				nF
				ns
				ns
				ns
				ns
			450	ns
t_f	Fall Time	$T_J=25$	60	ns
		T_{J450}	80	ns

V_{GE} V

Figure 3. Typical Transfer characteristics IGBT

R_g μ s

Figure 4. Switching Energy vs Gate Resistor IGBT

mJ

$V_F(V)$

Figure 9. Diode Forward Characteristics Diode

$R_g \text{ } \mu\text{s}$

Figure 10. Switching Energy vs Gate Resistor Diode

